

High Voltage Standard Rectifier

$$V_{RRM} = 2200\text{ V}$$

$$I_{FAV} = 30\text{ A}$$

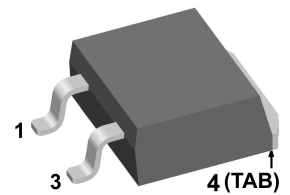
$$V_F = 1.24\text{ V}$$

Single Diode

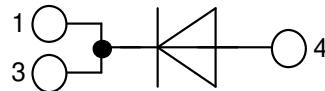
Part number

DNA30EM2200PZ

Marking on Product: DNA30EM2200PZ



Backside: anode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

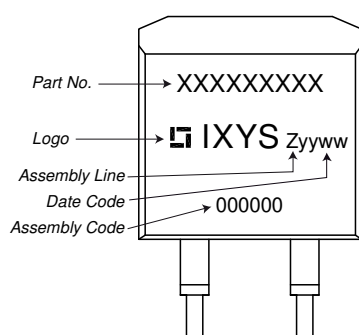
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				2200	V
I_R	reverse current	$V_R = 2200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	μA
		$V_R = 2200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.26	V
		$I_F = 60\text{ A}$				1.53	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.24	V
		$I_F = 60\text{ A}$				1.63	V
I_{FAV}	average forward current	$T_C = 140^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			30	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.83	V
r_F	slope resistance					13.4	m Ω
R_{thJC}	thermal resistance junction to case					0.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				210	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			370	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			400	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			315	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			340	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			685	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			665	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			495	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			480	A ² s
C_J	junction capacitance	$V_R = 700\text{ V}; f = 1\text{ MHz}$			7		pF

Package TO-263 (D2Pak-HV)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/Apb}$		terminal to backside	4.7			mm

Product Marking



Part description

D = Diode
 N = High Voltage Standard Rectifier
 A = ($\geq 2000V$)
 30 = Current Rating [A]
 EM = Single Diode
 2200 = Reverse Voltage [V]
 PZ = TO-263AB (D2Pak) (2HV)

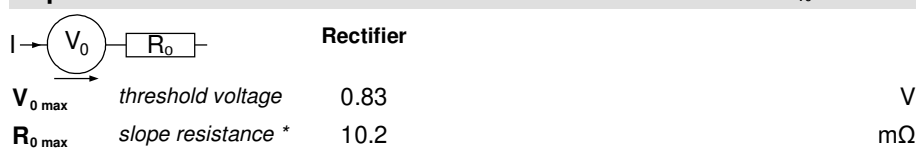
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DNA30EM2200PZ-TRL	DNA30EM2200PZ	Tape & Reel	800	514467
Alternative	DNA30EM2200PZ-TUB	DNA30EM2200PZ	Tube	50	525368

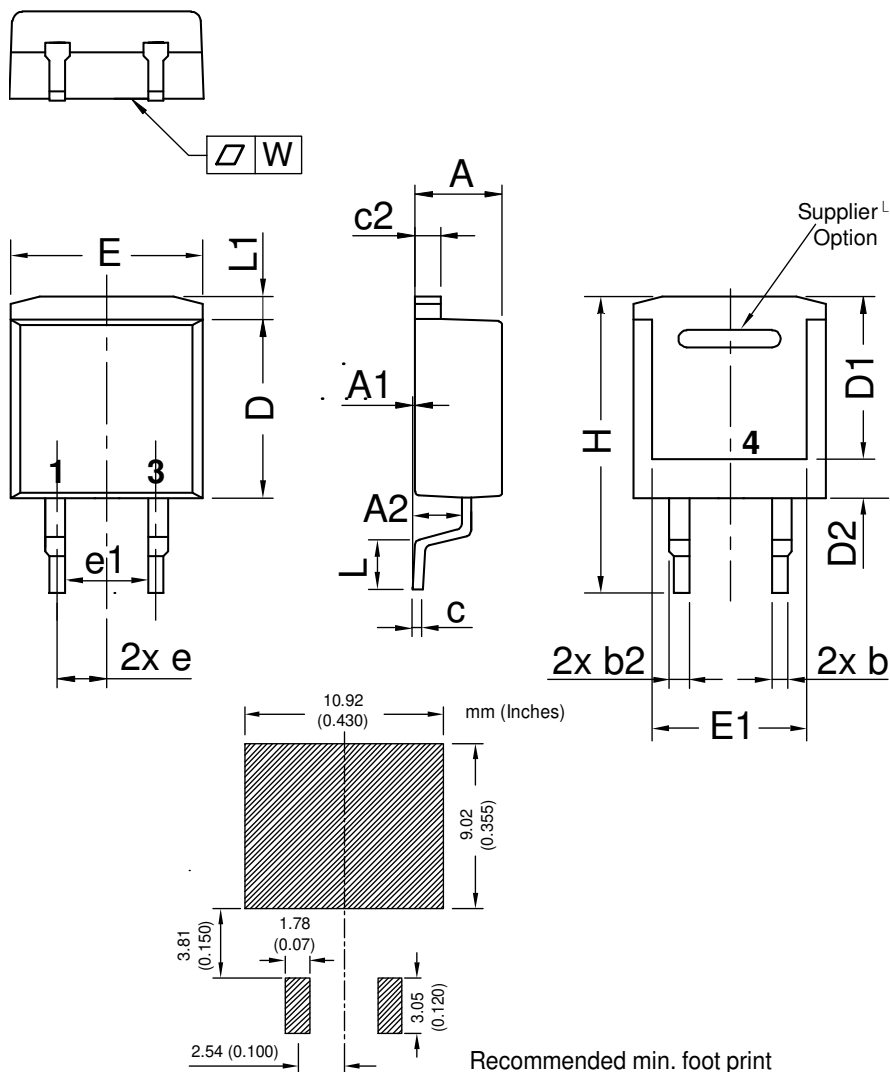
Similar Part	Package	Voltage class
DNA30E2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30E2200PA	TO-220AC	2200
DNA30E2200FE	i4-Pac (2HV)	2200
DNA30E2200IY	TO-262 (I2Pak) (2HV)	2200

Equivalent Circuits for Simulation

* on die level

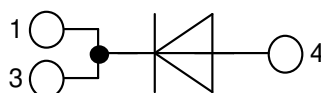
$T_{VJ} = 175^\circ C$



Outlines TO-263 (D2Pak-HV)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



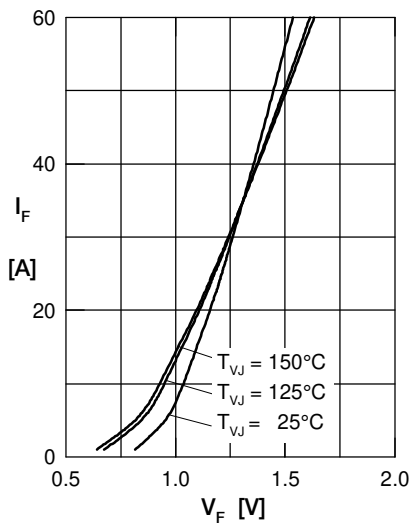
Rectifier


Fig. 1 Forward current versus voltage drop per diode

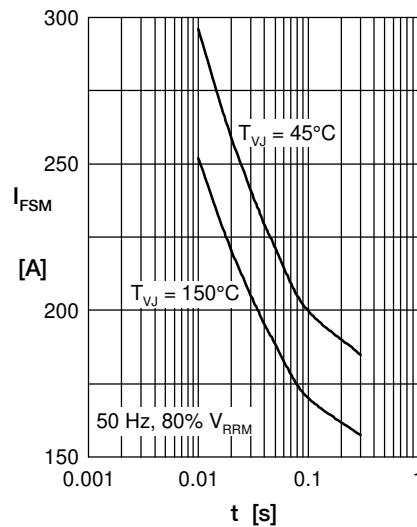


Fig. 2 Surge overload current

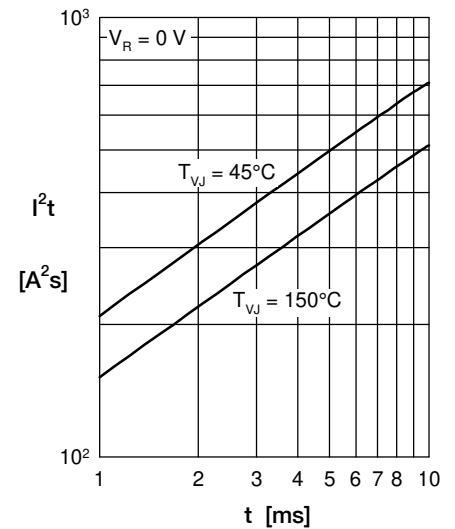
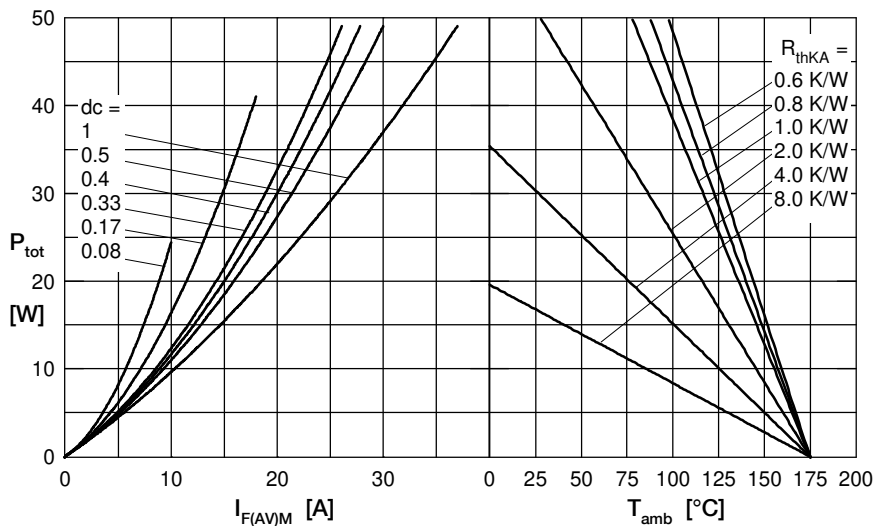

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current & ambient temperature

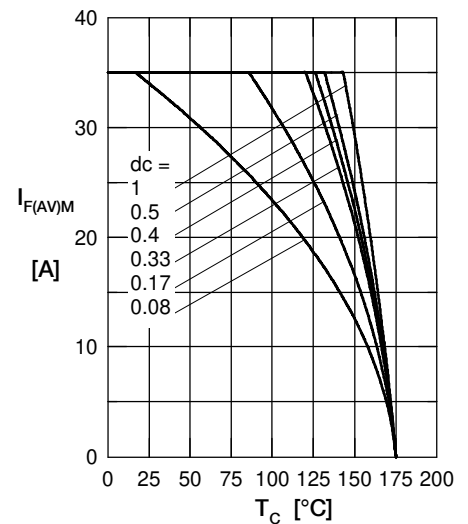


Fig. 5 Max. forward current versus case temperature

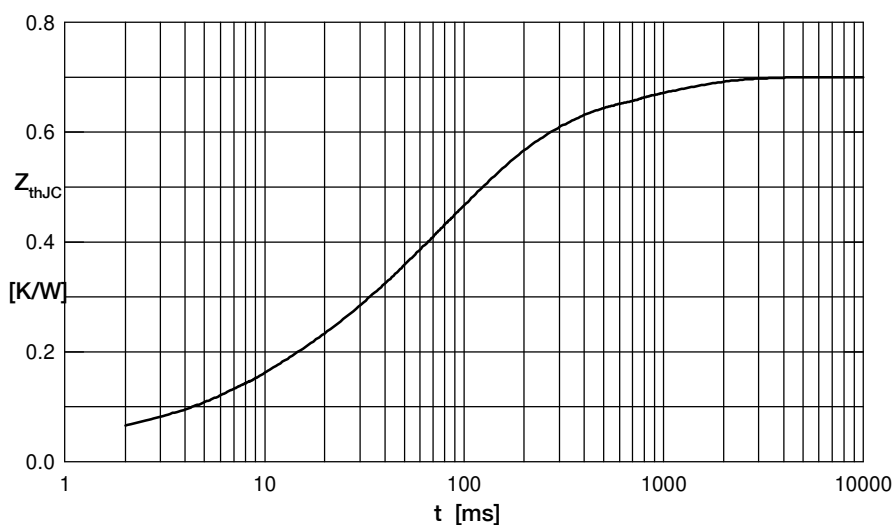


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.03	0.0003
2	0.072	0.0065
3	0.131	0.027
4	0.367	0.105
5	0.1	0.8